

Schottky barrier diode

RB160L-60

●Applications

High frequency rectification
For switching power supply.

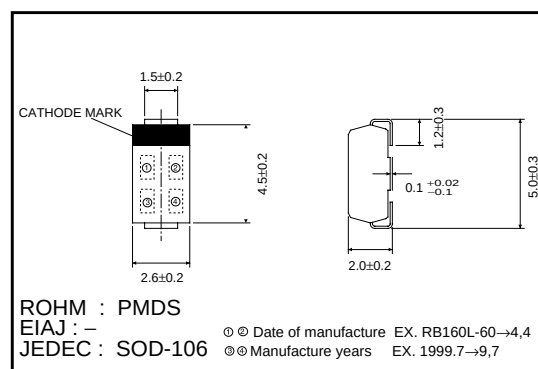
●Features

- 1) Compact power mold (PMDS)
- 2) Low V_F . ($V_F=0.55V$ Typ. at 1A)
- 3) High reliability

●Construction

Silicon epitaxial Planar

●External dimensions (Units : mm)



●Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	60	V
DC reverse voltage	V_R	60	V
Mean rectifying current *	I_O	1	A
Peak forward surge current	I_{FSM}	30	A
Junction temperature	T_J	125	$^\circ C$
Storage temperature	T_{stg}	$-40 \sim +125$	$^\circ C$

* When mounted on a PCBs board

●Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.58	V	$I_F = 1.0A$
Reverse current	I_R	—	—	0.5	mA	$V_R = 60V$

Diodes

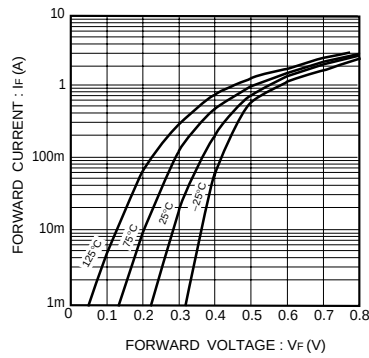
● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Forward characteristics

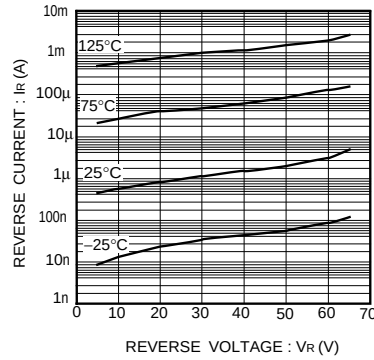


Fig.2 Reverse characteristics

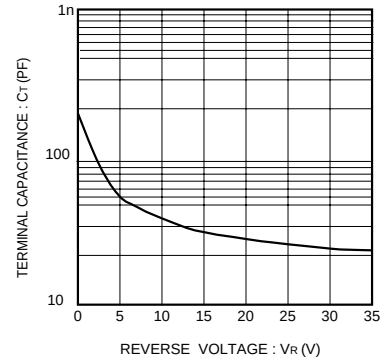
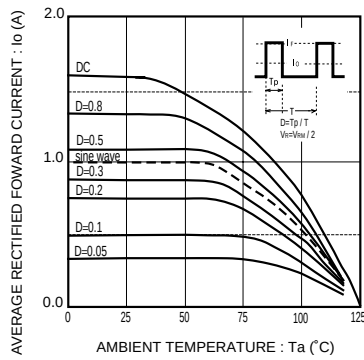
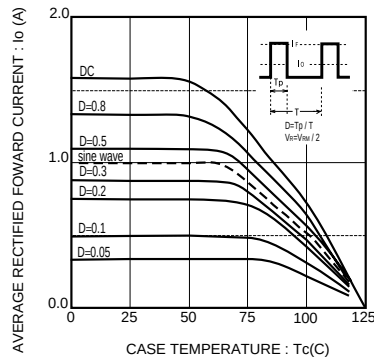


Fig.3 Capacitance between terminals characteristics

Fig.4 Derating curve (I_o - T_a)Fig.5 Derating curve (I_o - T_c)